

EAST-10648510 dual CCWsp.1

FileViewEditToolsWindowHelp

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(1) 09/948877

(1738) "KONINKLIJKE PHILIPS".as.

(0) 10/648510

(115127) (control adj (gate electrode plate) CG )

(64751) ((float \$4 adj (gate electrode plate trap \$4) FG) charge adj storage)

(64751) ((float \$4 adj (gate electrode plate trap \$4) FG) charge adj storage )

(615188) (sidewall side )

(4605362) different opposite

(780580) (sidewall side D ) near (different opposite)

(4874757) second

(4493) second adj2 ((control adj (gate electrode plate) CG D )

(38) (second adj2 ((control adj (gate electrode plate) CG D

(6) (second adj2 ((control adj (gate electrode plate) CG D

(6) (second adj2 ((control adj (gate electrode plate) CG D

(0) 07/244854 08/956986 09/984718 10/214582 10/382772 10/648510

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(8) (second adj2 ((control adj (gate electrode plate) CG D

(651886) (select control) adj (gate electrode plate) CG sg )

(8008617) two second another

(3237) (two second another) adj ((select control) adj (gate electrode plate) CG sg D )

(68183) ((float \$4 adj (gate electrode plate trap \$4) FG) charge adj storage)

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DBs:USPAT:US POPUB:EPO:JPO:DERWENT:IBM:TDG

Default operator:OR

Plerals

Highlight all hit terms initially

("6567315" "6403494" "6159798" "6373095" ).pn.

Sept 2004

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	U	I	inventor	Document ID	Issue	P	Title	Current	Current XE	Retrieval	S	C	P	P	P	P	P	Image Doc	P
1			Takase, Yosh	US 6567315 B2	200302		Nonvolatile memory and method of program	385/185	385/185.13									US 656731	
2			Chu, Wen-Tin	US 6403494 B1	200201		Method of forming a floating gate self-aligne	438/718	438/257									US 640349	
3			Bracchitta, J	US 6373095 B1	200208		NVRAM cell having increased coupling ratio	257/316	257/315									US 637309	
4			Dietz, Guido	US 6159796 A	200001		Method of forming a non-volatile memory cel	438/257	257/E21.20									US 615979	
5			KANAMITSU	JP 2002197876 A	20040		Write method in non-volatile memory, involve												
6			CHANG, C et	US 6403494 B	20020		Floating gate formation in split-gate flash me												
7			BRACCHITT	JP 11274439 A	19991		Non-volatile RAM cell used for digital calcula												
8			DIETZ, G et a	DE 19732870 A	20040		Semiconductor read-only memory cell, e.g. E												

Ready

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